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(54) Title: CLEANING SOLUTION FOR SEMICONDUCTOR SURFACES FOLLOWING CHEMICAL-MECHANICAL POLISHING

(57) Abstract: A composition and method are provided for cleaning contaminants from the surface of a semiconductor wafer after the wafer has been chemically-mechanically polished. The cleaning composition comprises a carboxylic acid, an amine-containing compound, a phosponic acid, and water. The cleaning composition is useful in removing abrasive remnants as well as metal contaminants from the surface of a semiconductor wafer following chemical-mechanical polishing.